



501.26244CC7

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: MURATA, et al.
Serial No.: 09/998,654
Filed: December 3, 2001
For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE HAVING
SWITCHING MISFET AND CAPACITOR ELEMENT AND
METHOD OF PRODUCING THE SAME, INCLUDING WIRING
THEREFOR AND METHOD OF PRODUCING SUCH WIRING
Group: 2812
Examiner: H. Tsai

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, A 22313-1450

RECEIVED
JUL 25 2003
SEMICONDUCTOR CENTER 2800
July 24, 2003

Sir:

In response to the Office Action mailed January 24, 2003, please amend the
above-identified application as follows:

IN THE CLAIMS

Please amend the claims presently in the application as follows:

1. (Amended) A method of producing a semiconductor integrated circuit
device having word lines, data lines and a plurality of memory cells each connected to
one of the word lines and one of the data lines, each of said plurality of memory cells
having (1) a MISFET having a gate electrode and a source region and a drain region on